课程大纲 COURSE SYLLABUS			
1.	课程代码/名称 Course Code/Title	先进半导体材料/Advanced semiconductor materials	
2.	课程性质 Compulsory/Elective	专业选修课	
3.	课程学分/学时 Course Credit/Hours	3 credit /48 hours	
4.	授课语言 Teaching Language	English	
5.	授课教师 Instructor(s)	尹龙卫 / Yin Longwei	
6.	是否面向本科生开放 Open to undergraduates or not	No	
7.	先修要求 Pre-requisites	No	
8.	教学目标 Course Objectives		
	The course is to reveal and study the micro mechanism of semiconductor and explain the macroscopic physical phenomena that occur in semiconductors from a microscopic point of view; to study the electronic state and motion law in semiconductors; to study the statistical distribution, transport theory and related laws of carriers in semiconductors; to learn some macroscopic physical phenomena that occur in the transport of carriers; and to learn some basic structures of semiconductors, including metal semiconductor junctions and surface problems. This course is to let students to master the nature and preparation methods of the main semiconductor materials, understand the latest development of semiconductor materials, for the work of semiconductor material science, semiconductor device preparation to lay a foundation for the future.		
9.	教学方法 Teaching Methods		
	 Most of the chapters in the course will be taught in English, while some chapters will be taught in bilingual education mode for students to better learn and master the content of the course. Interactive teaching will be introduced during the course process, the students are active with full participation, and self-presentation by students are invited on the relation between the course and their research subject. Latest research results and literature on the progress in semiconductor materials and devices will be involved and reviewed. 		
10.	教学内容 Course Contents		
	Section 1 State of electrons in semiconductors	 Lecture 1 Course introduction and general review of semiconductor materials Lecture 2 State of electrons in semiconductors Lecture 3 Electroconductive mechanism of holes in intrinsic semiconductors, energy band structure of silicon and germanium 	
	Section 2 Impurities and defect levels in semiconductors	Lecture 4 Impurities in semiconductors Lecture 5 Defect levels in semiconductors Lecture 6 Statistical distribution of carriers in semiconductors, carrier concentration of the intrinsic semiconductor Lecture 7 Carrier concentration of impurity semiconductors Lecture 8 Conductivity of semiconductors, drift mobility of carriers, carrier scattering	

		Lecture 9 Conductivity of semiconductors, resistivity and its relation to impurity concentration and temperatureLecture 10 Effects under a strong electric field, thermal carriers
	Section 3 Non-equilibrium carriers and p-n junction	 Lecture 11 Non-equilibrium carriers, injection and recombination of non-equilibrium carriers Lecture 12 Lifetimes of non-equilibrium carriers, quasi-Fermi level, Lecture 13 Non-equilibrium carriers, composite theory, trap effect, Einstein relation of the drift motion of the carrier Lecture 14 p-n junction, heterojunction and its band diagram, carrier transport mechanism of heterojunction
	Section 4 Metal and semiconductor contacts	Lecture 15 Metal and semiconductor contacts, metal and semiconductor contact and its energy band map, rectifier theory of metal-semiconductor contact, Ohmic contact
	Section 5 Semiconductor surface and MIS structure	Lecture 16 Surface state, surface electric field effect, capacitive voltage characteristics of the MIS structure, property of the silicon-silica system
	Section 6 Photoelectric properties, photoelectricity and luminescence of semiconductors	Lecture 17 Optical absorption and photo conductivity of semiconductors, photovolt effect of semiconductors, Semiconductor luminescence and laser
	Section 7 Thermoelectric properties of semiconductors	Lecture 18 Thermo-electric properties of Semiconductor, application of thermoelectric effect
	Section 8 Semiconductor magnetic and piezoresistive effects	Lecture 19 Hall effect, magnetoresistivity, photomagnetoelectric effect, electroresistive effect
	Section 9 Semiconductor materials	Lecture 20 Semiconductor materials, technical requirements for semiconductor materials, Lecture 21 Preparation of semiconductor materials
	Section 10 Semiconductor devices	Lecture 22 Semiconductor diode Lecture 23 Semiconductor triode Lecture 24 Field-effect transistor
11.	课程考核 Course Assessment	
	Class participation / Quiz: 15% Homework: 25% Midterm: 25% Final: 35%	
12.	教材及其它参考资料 Textbook and Supplementar	y Readings
	1.《半导体物理学》(第六版) 2.《半导体物理与器件》(第),刘恩科等编著,电子工业出版社。 第三版),Donald A.Neamen 著,电子工业出版社。